FORMULATION FOR REMOVAL OF PHOTORESIST, ETCH RESIDUE AND BARC

ABSTRACT OF THE DISCLOSURE

A formulation for removing photoresist, ion implanted photoresist, etch residue or BARC comprises: an ammonium hydroxide and a 2-aminobenzothiazole, remainder water. Preferably the formulation comprises: tetramethyl ammonium hydroxide, tolyltriazole, propylene glycol, 2-aminobenzothiazole, dipropylene glycol monomethyl ether, remainder water; more preferably: tetramethyl ammonium hydroxide 1-15 wt %, tolyltriazole 1-5 wt%, propylene glycol 5-15 wt%, 2-aminobenzothiazole 1-10 wt%; dipropylene glycol monomethyl ether 20-45 wt%, remainder water. The invention is also a method of removing materials selected from the group consisting of photoresist, etch residue, BARC and combinations thereof, from a substrate comprising: applying a formulation, described above, to the substrate to remove the material from the substrate.